

Please amend the claims as follows. This Listing of Claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A method for cleaning and drying a front and a back surface of a semiconductor substrate, the method comprising:

brush scrubbing the back surface of the semiconductor substrate using a brush scrubbing chemistry;

forming a front fluid meniscus with the front surface of the semiconductor substrate and a back fluid meniscus with the back surface of the semiconductor substrate, the forming of the front and the back fluid menisci being performed after the brush scrubbing of the back surface; and

scanning the front surface of the semiconductor substrate and the back surface of the semiconductor substrate by moving the front meniscus along the front surface of the semiconductor substrate and the back fluid meniscus along the back surface of the semiconductor substrate, the front and back fluid menisci including being formed using a chemistry that is compatible with the brush scrubbing chemistry,

wherein scanning the front surface of the substrate and the back surface of the substrate is configured to clean and dry the front surface of the substrate and the back surface of the substrate.

Claim 2 (Currently Amended): A method as recited in claim 1, wherein the chemistry included in the front ~~and back menisci~~ meniscus being compatible with the brush scrubbing chemistry prevents chemical contamination of the front surface of the semiconductor substrate.

Claim 3 (Previously Presented): A method as recited in claim 2, wherein chemical contamination causes particulate contaminants or undesirable etching of the semiconductor substrate front surface.

Claim 4 (Previously Presented): A method as recited in claim 1, wherein forming the front fluid meniscus and the back fluid meniscus is configured to occur simultaneously.

Claim 5 (Previously Presented): A method as recited in claim 1, wherein the operation of scanning the front surface of the semiconductor substrate and the back surface of the semiconductor substrate is configured to occur synchronously.

Claim 6 (Currently Amended): A method as recited in claim 2, wherein a chemistry of the front fluid meniscus includes a front cleaning chemistry and a chemistry of the back fluid meniscus includes a back cleaning chemistry.

Claim 7 (Previously Presented) A method as recited in claim 6, wherein the brush scrubbing chemistry includes hydrofluoric acid.

Claim 8 (Original): A method as recited in claim 7, wherein the front cleaning chemistry includes hydrofluoric acid.

Claim 9 (Previously Presented): A method as recited in claim 1, wherein each of the front fluid meniscus and the back fluid meniscus includes isopropyl alcohol (IPA) vapor, nitrogen, organic compounds, hexanol, ethylglycol, or compounds mixable with water.

Claim 10 (Currently Amended): A method for preparing a semiconductor substrate, the method comprising:

brush scrubbing a back surface of the semiconductor substrate using a brush scrubbing chemistry; and

upon completing the brush scrubbing of the back surface, applying a front fluid meniscus onto a front surface of the semiconductor substrate, the front fluid meniscus including being formed using a front cleaning chemistry, the front cleaning chemistry being chemically compatible with the brush scrubbing chemistry.

Claim 11 (Previously Presented): A method as recited in claim 10, the method further comprising:

scanning the front surface of the semiconductor substrate by moving the front meniscus along the front surface of the semiconductor substrate.

Claim 12 (Previously Presented): A method as recited in claim 10, the method further comprising:

applying a back fluid meniscus onto the back surface of the semiconductor substrate, the back fluid meniscus including being formed using a back cleaning chemistry, the back cleaning chemistry being chemically compatible with the brush scrubbing chemistry.

Claim 13 (Previously Presented): A method as recited in claim 12, the method further comprising:

scanning the back surface of the semiconductor substrate by moving the back fluid meniscus along the back surface of the semiconductor substrate.

Claim 14 (Currently Amended): A method as recited in claim 10, wherein the front chemistry ~~and the back chemistry of the front and back fluid menisci are~~ is configured to be compatible with the brush scrubbing chemistry so as to prevent chemical contamination of the front surface of the semiconductor substrate.

Claim 15 (Original): A method as recited in claim 14, wherein chemical contamination causes particulate contaminants.

Claim 16 (Previously Presented): A method as recited in claim 13, wherein scanning the front surface of the semiconductor substrate and the back surface of the semiconductor substrate is configured to occur synchronously.

Claims 17-23 (Cancelled)

Claim 24 (Currently Amended): A method for preparing a semiconductor substrate, the method comprising:
brush scrubbing a back surface of the semiconductor substrate using a brush scrubbing chemistry; and
upon completing the brush scrubbing of the back surface, applying a front fluid meniscus onto a front surface of the semiconductor substrate, the front fluid meniscus including being formed using a front cleaning chemistry, the front cleaning chemistry being chemically compatible with the brush scrubbing chemistry so as to prevent chemical contamination of the front surface of the semiconductor substrate,

wherein the brush scrubbing chemistry includes hydrofluoric acid and the front cleaning chemistry includes hydrofluoric acid.

Claim 25 (Previously Presented): A method as recited in claim 24, the method further comprising:

scanning the front surface of the semiconductor substrate by moving the front meniscus along the front surface of the semiconductor substrate.

Claim 26 (Currently Amended): A method as recited in claim 24, the method further comprising:

applying a back fluid meniscus onto the back surface of the semiconductor substrate, the back fluid meniscus including being formed using a back cleaning chemistry, the back cleaning chemistry being chemically compatible with the brush scrubbing chemistry.

Claim 27 (Previously Presented): A method as recited in claim 26, the method further comprising:

scanning the back surface of the semiconductor substrate by moving the back meniscus along the back surface of the semiconductor substrate.

Claim 28 (Previously Presented): A method as recited in claim 27, wherein the back chemistry of the back fluid meniscus is configured to be compatible with the brush scrubbing chemistry so as to prevent chemical contamination of the front surface of the semiconductor substrate.